

MOS FIELD EFFECT TRANSISTOR

2SK4091

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK4091 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

FEATURES

- Low on-state resistance
 $R_{DS(on)1} = 13.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 15 \text{ A)}$
 $R_{DS(on)2} = 21 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 15 \text{ A)}$
- Low gate to drain charge
 $Q_{GD} = 2.2 \text{ nC TYP. (} V_{DD} = 15 \text{ V, } I_D = 30 \text{ A)}$
- 4.5 V drive available
- Avalanche capability ratings

ORDERING INFORMATION

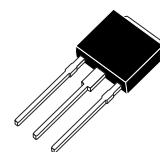
PART NUMBER	LEAD PLATING	PACKING	PACKAGE
2SK4091(1)-S27-AY ^{Note}	Pure Sn (Tin)	Tube 75 p/tube	TO-251 (MP-3-b) typ. 0.34 g
2SK4091-ZK-E1-AY ^{Note}		Tape 2500 p/reel	TO-252 (MP-3ZK) typ. 0.27 g
2SK4091-ZK-E2-AY ^{Note}			

Note Pb-free (This product does not contain Pb in external electrode).

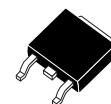
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _c = 25°C)	I _{D(DC)}	±30	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±110	A
Total Power Dissipation (T _c = 25°C)	P _{T1}	21	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current ^{Note2}	I _{AS}	18	A
Single Avalanche Energy ^{Note2}	E _{AS}	32.4	mJ

(TO-251)



(TO-252)



Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω, V_{GS} = 20 → 0 V, L = 0.1 mH

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

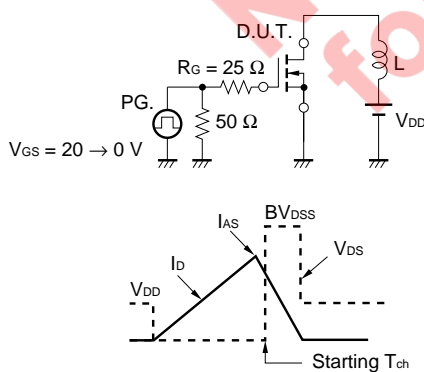
Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

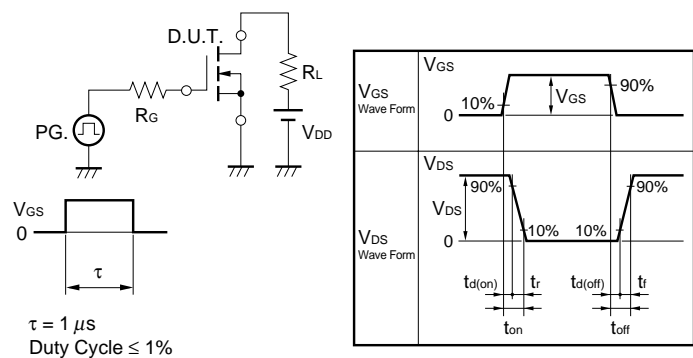
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 15 A	7	14		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = 10 V, I _D = 15 A		9.8	13.0	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 15 A		13.6	21	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V,		920		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V,		240		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		78		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 30 A,		7.5		ns
Rise Time	t _r	V _{GS} = 10 V,		3.9		ns
Turn-off Delay Time	t _{d(off)}	R _G = 3 Ω		26		ns
Fall Time	t _f			4.8		ns
Total Gate Charge	Q _{G1}	V _{DD} = 15 V, V _{GS} = 10 V, I _D = 30 A		15		nC
	Q _{G2}	V _{DD} = 15 V, V _{GS} = 4.5 V, I _D = 30 A		6.7		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 15 V, I _D = 30 A		2.6		nC
Gate to Drain Charge	Q _{GD}			2.2		nC
Gate Resistance	R _G			1.6		Ω
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 30 A, V _{GS} = 0 V		0.9	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, V _{GS} = 0 V,		25		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		16		nC

Note Pulsed

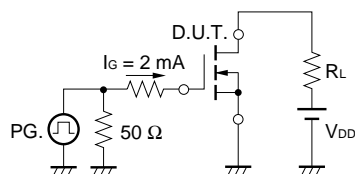
TEST CIRCUIT 1 AVALANCHE CAPABILITY



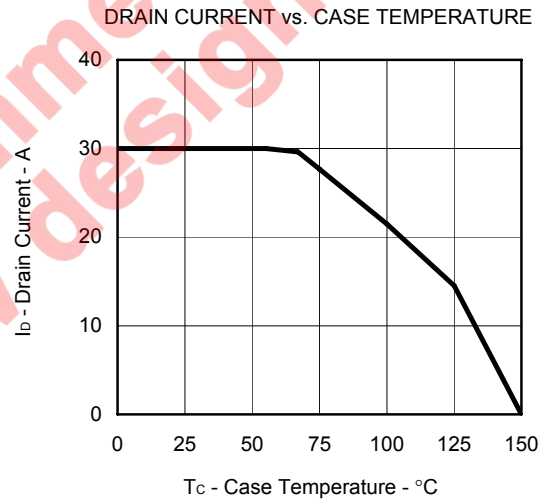
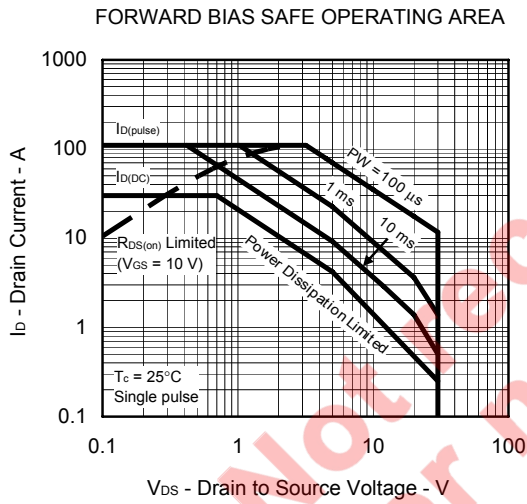
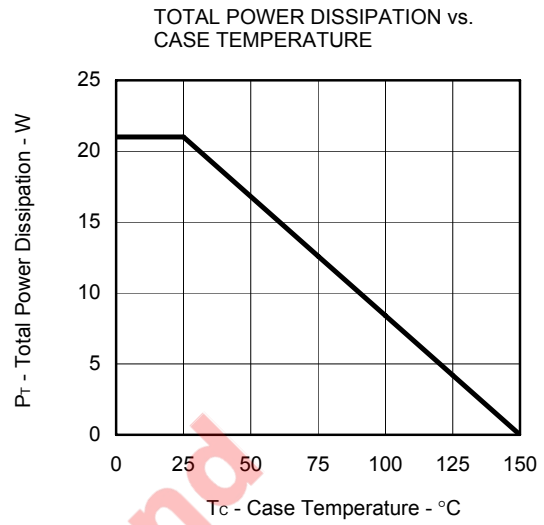
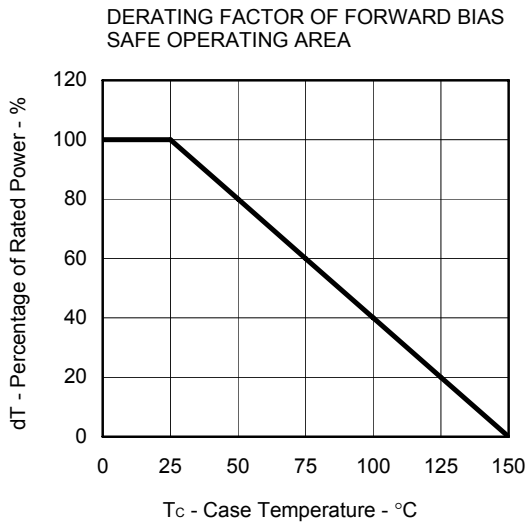
TEST CIRCUIT 2 SWITCHING TIME



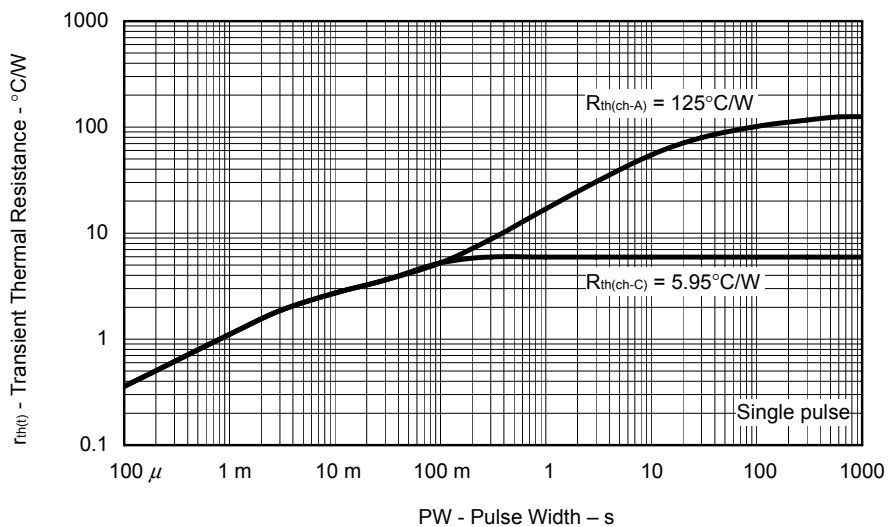
TEST CIRCUIT 3 GATE CHARGE



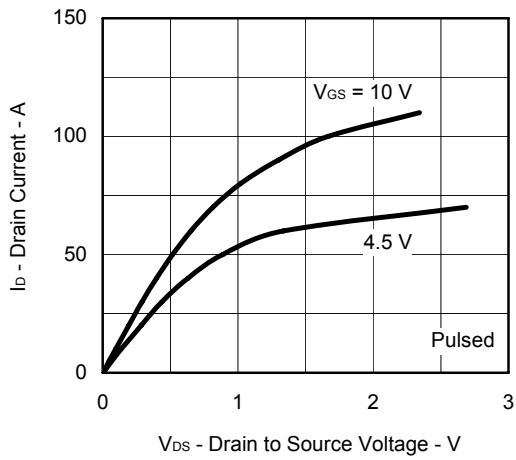
TYPICAL CHARACTERISTICS (T_A = 25°C)



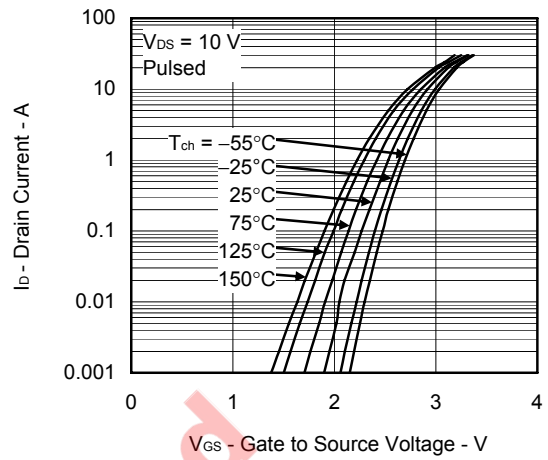
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



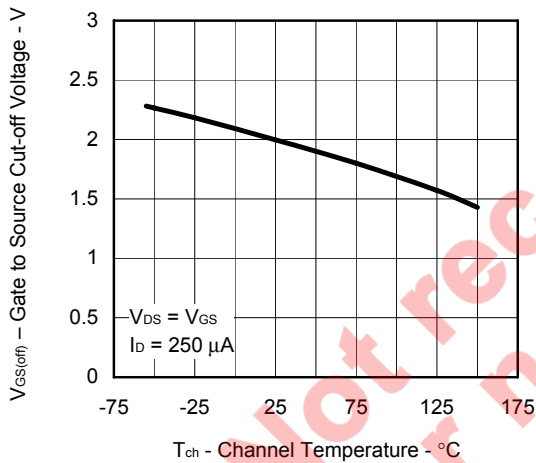
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



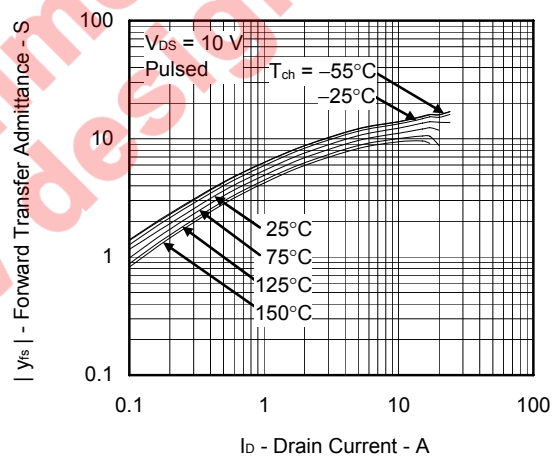
FORWARD TRANSFER CHARACTERISTICS



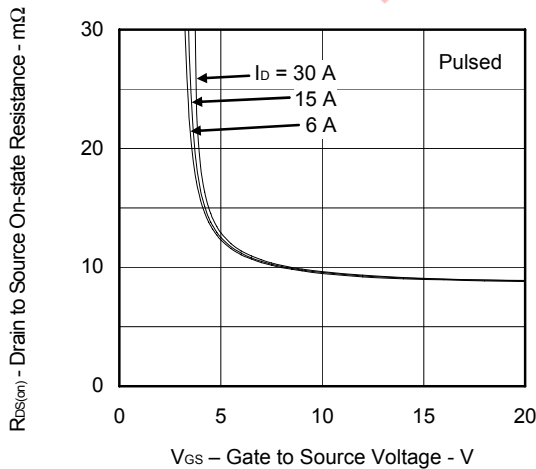
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



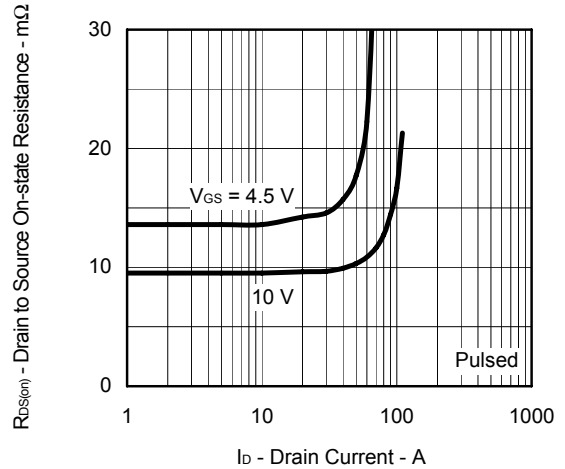
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



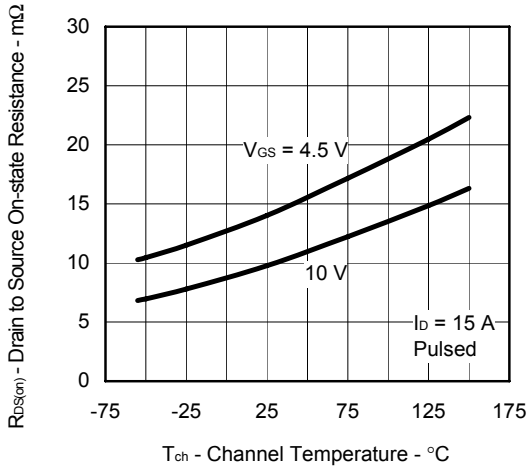
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



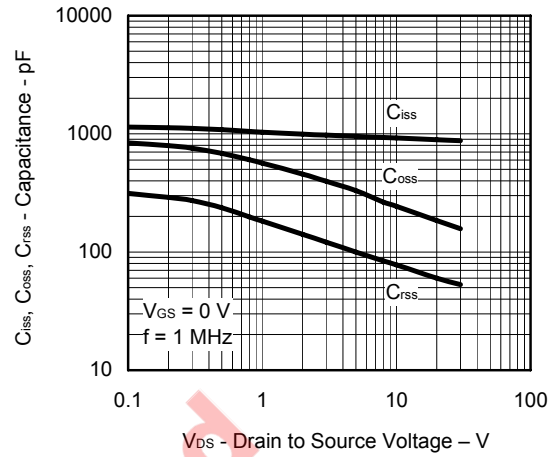
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



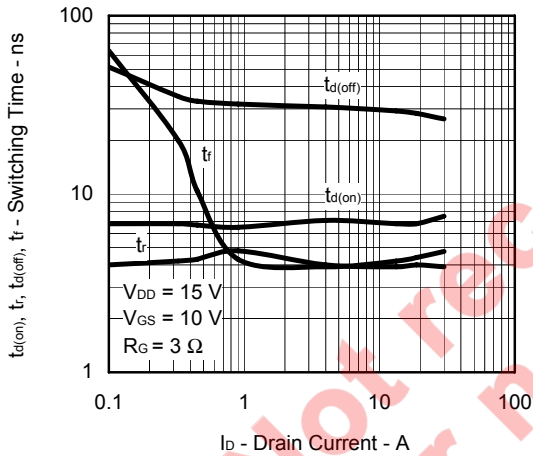
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



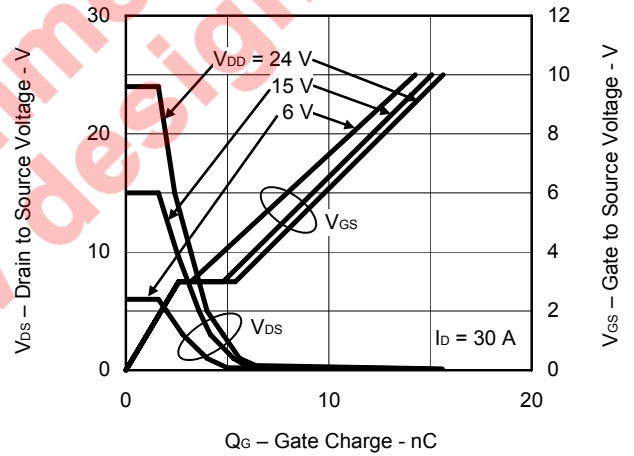
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



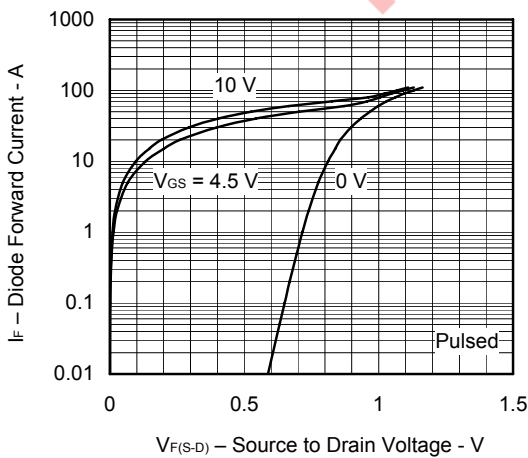
SWITCHING CHARACTERISTICS



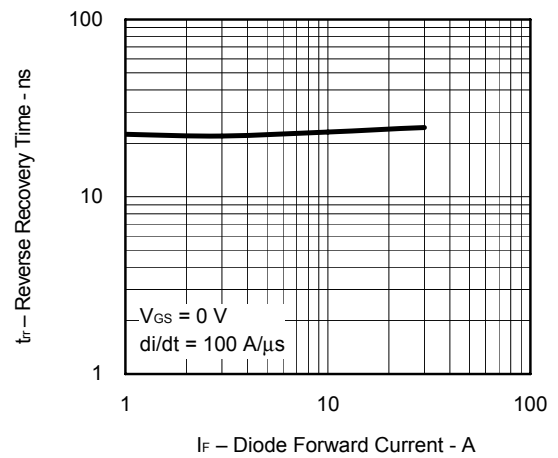
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



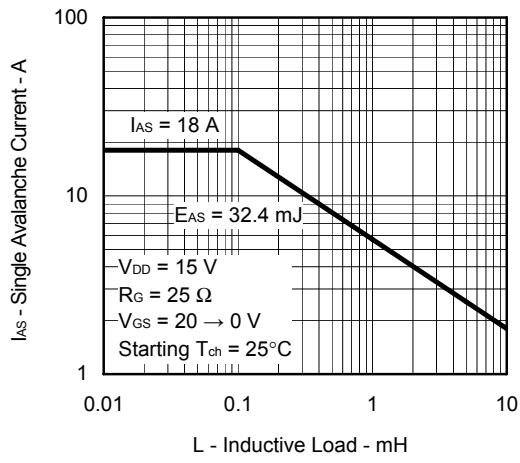
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



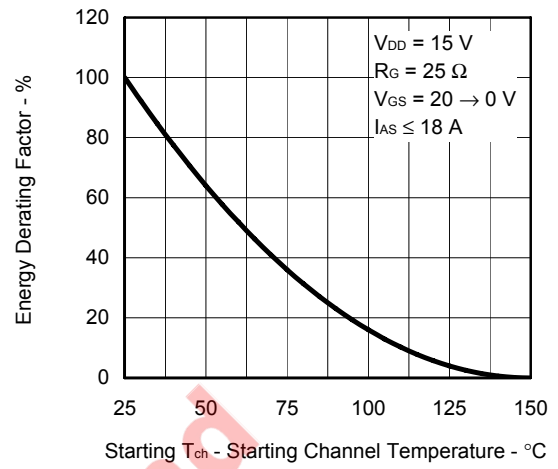
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



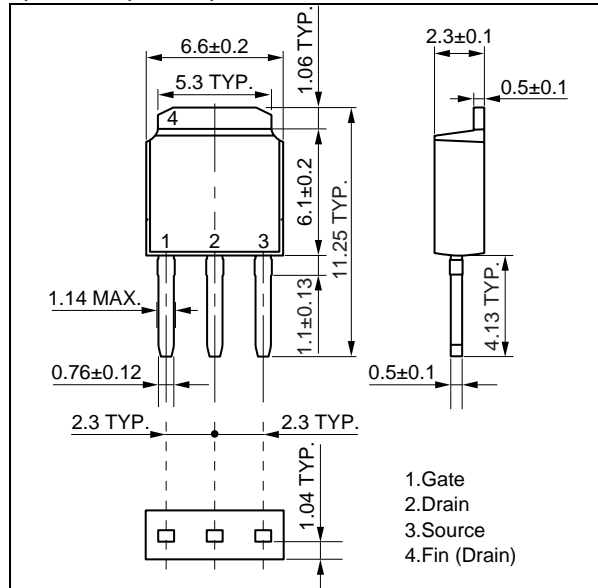
SINGLE AVALANCHE ENERGY DERATING FACTOR



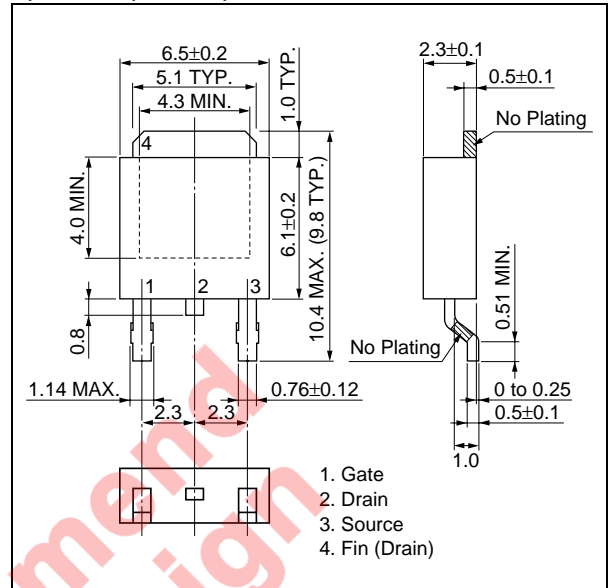
Not recommended for new design

PACKAGE DRAWINGS (Unit: mm)

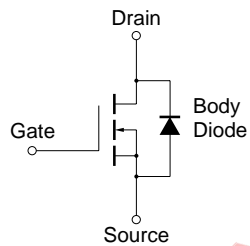
1) TO-251 (MP-3-b)



2) TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.